

June 2009

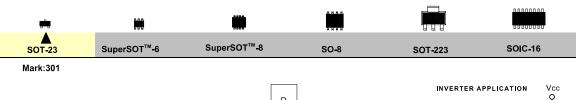
FDV301N Digital FET , N-Channel

General Description

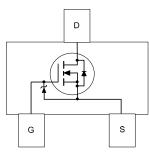
This N-Channel logic level enhancement mode field effect transistor is produced using Fairchild's proprietary, high cell density, DMOS technology. This very high density process is especially tailored to minimize on-state resistance. This device has been designed especially for low voltage applications as a replacement for digital transistors. Since bias resistors are not required, this one N-channel FET can replace several different digital transistors, with different bias resistor values.

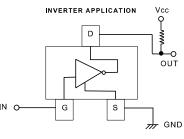
Features

- $\begin{tabular}{ll} \blacksquare 25 V, 0.22 A continuous, 0.5 A Peak. \\ $R_{\rm DS(ON)} = 5 \ \Omega \ @ \ V_{\rm GS} = 2.7 \ V \\ $R_{\rm DS(ON)} = 4 \ \Omega \ @ \ V_{\rm GS} = 4.5 \ V. \end{tabular}$
- Very low level gate drive requirements allowing direct operation in 3V circuits, V_{GS(th)} < 1.06V.
- Gate-Source Zener for ESD ruggedness.>6kV Human Body Model
- Replace multiple NPN digital transistors with one DMOS FET.









Absolute Maximum Ratings T_A = 25°C unless other wise noted

Symbol	Parameter	FDV301N	Units
V _{DSS} , V _{CC}	Drain-Source Voltage, Power Supply Voltage	25	V
V _{GSS} , V _I	Gate-Source Voltage, V _{IN}	8	V
I _D , I _O	Drain/Output Current - Continuous	0.22	А
		0.5	
P _D	Maximum Power Dissipation	0.35	W
T _J ,T _{STG}	Operating and Storage Temperature Range	-55 to 150	°C
ESD	Electrostatic Discharge Rating MIL-STD-883D Human Body Model (100pf / 1500 Ohm)	6.0	kV
THERMA	L CHARACTERISTICS		<u>.</u>
R _{eua}	Thermal Resistance, Junction-to-Ambient	357	°C/W

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Symbol	Parameter	Conditions	Min	Тур	Max	Units
O (off)	Zero Input Voltage Output Current	$V_{CC} = 20 \text{ V}, V_{I} = 0 \text{ V}$			1	μΑ
V _{I (off)}	Input Voltage	$V_{cc} = 5 \text{ V}, I_{o} = 10 \mu\text{A}$			0.5	V
V _{I (on)}	7	$V_0 = 0.3 \text{ V}, I_0 = 0.005 \text{ A}$	1			V
R _{O (on)}	Output to Ground Resistance	$V_1 = 2.7 \text{ V}, \ I_0 = 0.2 \text{ A}$		4	5	Ω
Electrica	al Characteristics (T _A = 25 °C unles	s otherwise noted)				
Symbol	Parameter	Conditions	Min	Тур	Max	Units
OFF CHAR	ACTERISTICS	·	•		•	•
BV _{DSS}	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	25			V
$\Delta BV_{DSS}/\Delta T_{J}$	Breakdown Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		25		mV / °C
I _{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20 \text{ V}, \ V_{GS} = 0 \text{ V}$ $T_{J} = 55^{\circ}\text{C}$			1	μA
					10	μΑ
GSS	Gate - Body Leakage Current	V _{GS} = 8 V, V _{DS} = 0 V			100	nA
	CTERISTICS (Note)		1	ı		
$\Delta V_{GS(th)}/\Delta T_{J}$	Gate Threshold Voltage Temp. Coefficient	I _D = 250 μA, Referenced to 25 °C		-2.1		mV / °C
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$	0,70	0,85	1,06	V
R _{DS(ON)}	Static Drain-Source On-Resistance	$V_{GS} = 2.7 \text{ V}, I_D = 0.2 \text{ A}$		3.8	5	Ω
DS(ON)		T ₁ =125°C		6.3	9	1
		$V_{GS} = 4.5 \text{ V}, I_D = 0.4 \text{ A}$		3.1	4	
I _{D(ON)}	On-State Drain Current	$V_{GS} = 2.7 \text{ V}, V_{DS} = 5 \text{ V}$	0.2			Α
9 _{FS}	Forward Transconductance	V _{DS} = 5 V, I _D = 0.4 A		0.2		S
	CHARACTERISTICS	50 5	1	ı		
C _{iss}	Input Capacitance	$V_{DS} = 10 \text{ V}, \ V_{GS} = 0 \text{ V}, $ f = 1.0 MHz		9.5		рF
C _{oss}	Output Capacitance	f = 1.0 MHz		6		рF
C _{rss}	Reverse Transfer Capacitance			1.3		pF
SWITCHING	CHARACTERISTICS (Note)	·	•		•	
t _{D(on)}	Turn - On Delay Time	$V_{DD} = 6 \text{ V}, I_D = 0.5 \text{ A},$		3.2	8	ns
t,	Turn - On Rise Time	$V_{GS} = 4.5 \text{ V}, R_{GEN} = 50 \Omega$		6	15	ns
$t_{D(off)}$	Turn - Off Delay Time			3.5	8	ns
t _f	Turn - Off Fall Time			3.5	8	ns
Q_g	Total Gate Charge	$V_{DS} = 5 \text{ V}, I_{D} = 0.2 \text{ A},$		0.49	0.7	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 4.5 V		0.22		nC
_	Gate-Drain Charge			0.07		nC
Q_{gd}	DOE DIODE OLIADA OTEDIOTICO AND 1443/84	JM RATINGS				
9-	IRCE DIODE CHARACTERISTICS AND MAXIMI					
9-	Maximum Continuous Drain-Source Diode Fo				0.29	Α

Typical Electrical Characteristics

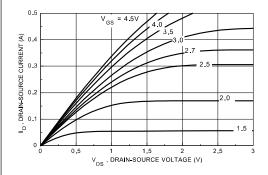


Figure 1. On-Region Characteristics.

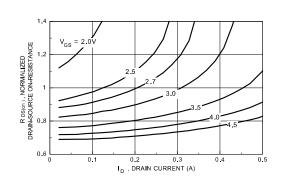


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

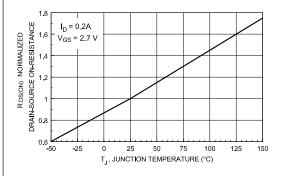


Figure 3. On-Resistance Variation with Temperature.

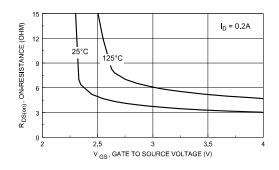


Figure 4. On Resistance Variation with Gate-To-Source Voltage.

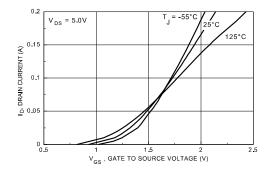


Figure 5. Transfer Characteristics.

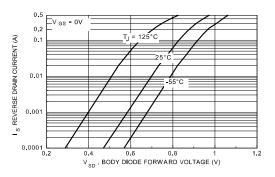


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

Typical Electrical And Thermal Characteristics

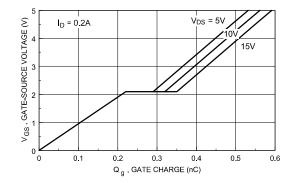


Figure 7. Gate Charge Characteristics.

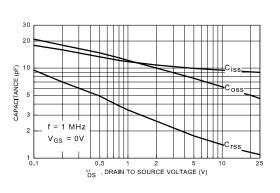


Figure 8. Capacitance Characteristics.

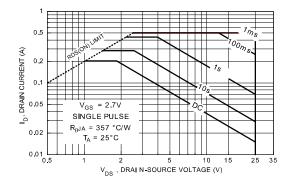


Figure 9. Maximum Safe Operating Area.

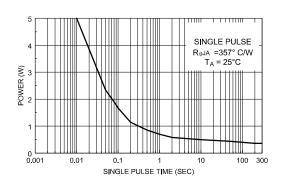


Figure 10. Single Pulse Maximum Power Dissipation.

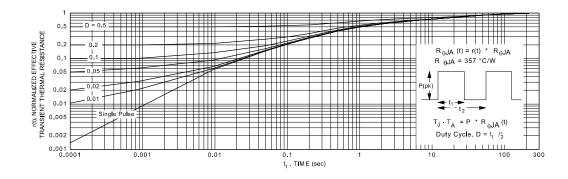


Figure 11. Transient Thermal Response Curve.



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